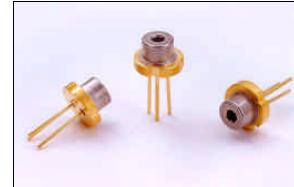


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S6505MG TECHNICAL DATA



Visible Wavelength Laserdiode

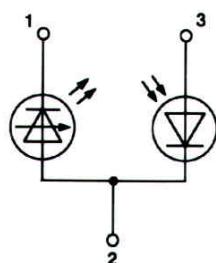
Structure InGaAlP, index guided single transverse mode

Lasing wavelength 655nm typ.

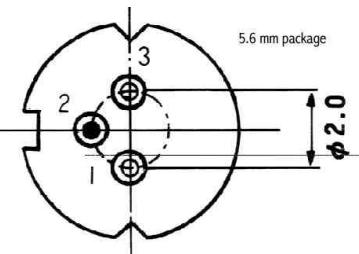
Output power 5 mW, CW

Package 5.6 mm MG, TO-18

PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	5	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operation Case Temperature	T _C	-10 .. +60	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I _{th}			25	45	mA
Operation Current	I _{op}	P _o = 5mW		28	48	mA
Operating Voltage	V _{op}	P _o = 5mW		2.2	2.8	V
Lasing Wavelength	λ _p	P _o = 5mW	650	655	660	nm
Beam Divergence	θ//	P _o = 5mW	5	7	9	°
Beam Divergence	θ⊥	P _o = 5mW	30	32	38	°
Slope Efficiency	η		0.5	0.7	1	mW/mA
Monitor Current	I _m	P _o = 5mW	50	200	500	μA